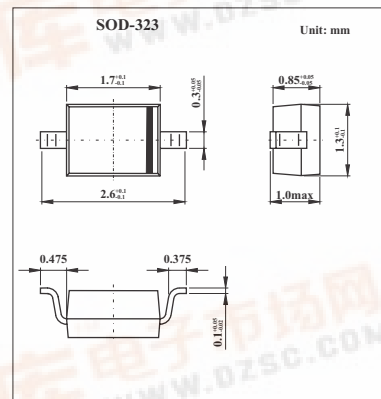


SMD Type Diodes

Silicon Epitaxial Planar Diode

KDV214



■ Features

- High Capacitance Ratio : C2V/C25V=6.5(Typ.)
- Low Series Resistance : rS=0.4 Ω (Typ.)
- Excellent C-V Characteristics, and Small Tracking Error.
- Useful for Small Size Tuner.

■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Value	Unit
Reverse Voltage	VR	32	V
Peak Reverse Voltage	VRM	35 (RL=10K Ω)	V
Junction Temperature	Tj	125	°C
Storage Temperature Range	Tstg	-55 to +125	°C

■ Electrical Characteristics Ta = 25 °C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Voltage	VR	IR = 1 μ A	30			V
Reverse Current	IR	VR = 28 V			10	nA
Capacitance	C2V	f = 1 MHz;VR = 2 V	14.16		16.25	pF
	C25V	f = 1 MHz;VR = 25 V	2.11		2.43	
Capacitance Ratio	C2V/C25V		5.9	6.5	7.15	
Series Resistance	rs	VR = 5V, f = 470 MHz		0.4	0.55	Ω

Note :

Available in matched group for capacitance to 2.5%.

$$\frac{C(\text{Max.})-C(\text{Min.})}{C(\text{Min.})} \leq 0.025$$

■ Marking

Marking	UO
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